

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(trench and mosfet and substrate and epitaxial and layer and concentration and than and body and etching and depositing and side and bottom and upper and surface and (lower or smaller) and (higher or greater) and mask and implanting and diffusing and . temperature and lining and insulating and source and sacrificial and oxide).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/24 16:58
L2	0	(trench and mosfet and substrate and epitaxial and layer and concentration and than and body and etching and depositing and side and bottom and upper and surface and (lower or smaller) and (higher or greater) and span\$2 and mask and implanting and diffusing and temperature and lining and insulating and source).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/24 17:00